



SDI Review Form 1.6

Journal Name:	Physical Science International Journal
Manuscript Number:	Ms_PSIJ_29024
Title of the Manuscript:	Influence of Annealing Temperature on the Physical Properties of Polycrystalline Cu₂SnSe₃ Thin Films Prepared by Thermal Vacuum Evaporation Technique
Type of the Article	Original Research Article

General guideline for Peer Review process:

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.

To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

(<http://www.sciencedomain.org/page.php?id=sdi-general-editorial-policy#Peer-Review-Guideline>)



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PART 1: Review Comments

	Reviewer's comment	Author's comment (if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)
Compulsory REVISION comments	<p>The paper shows results of thermally evaporated Cu₂SnSe₃. After different temperature annealing, a series of physical properties have been investigated. However, the paper needs a lot of improvements before it can be considered for the journal.</p> <ol style="list-style-type: none"> 1. Cu₂SnSe₃ is a popular material for photovoltaic application, which has been clearly stated in the introduction part by authors. However, there is no conclusive result about the band gap of the material. Authors show activation energy of 0.018 eV, using the annealing temperature as the reference. Authors should read more papers about activation energy calculation and photovoltaic effect. 2. No crystal structures results. Authors should at least give some XRD to confirm the Cu₂SnSe₃ phase. 3. Thermally evaporated Cu₂SnSe₃ has been extensively studied. Authors should consider more deep analysis of the system. 	<p>Noted and very well addressed by the reviewer. Thank you for your kind understanding for review this manuscript.</p> <p>Yes definitely we found that activation energy is 0.018 eV and also authors explain well about this earlier. We try to explain that the activation energy is the difference in energy content between atoms or molecules in an activated or transition-state configuration and the corresponding atoms and molecules in their initial configuration. In the context of semiconductors or insulators, it is called electronic band gap.</p> <p>Details XRD results for similar thin films has been published in other journal earlier. Thank you for reviewer suggestions. However, we try many techniques for using thermal evaporation method and tools that make it different and easier to be understood by readers</p>
Minor REVISION comments		
Optional/General comments		